



APPLICATION DATA SHEET

Electronic Version v14

Stylesheet Version v14.0

Title of Invention	[HIGH-VOLTAGE MOS DEVICE AND FABRICATION THEREOF]		
Application Type : regular, utility Attorney Docket Number : 13366-US-PA			
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Attorney Information: practitioner(s) at Customer Number: 31561  as my attorney(s) or agent(s) to prosecute the application identified above, and to transact all business in the United States Patent and Trademark Office connected therewith.			